



# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

The **ASI PT9700** is Designed for High Power Class C Amplifier, in 225 to 400 MHz Military Communication Equipment.

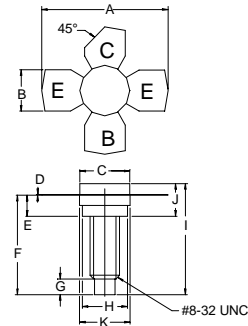
## FEATURES:

- Class C Operation
- $P_G = 13 \text{ dB}$  at 1.0 W/400 MHz
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

$I_C$	2.0 A
$V_{CBO}$	45 V
$V_{CEO}$	25 V
$V_{EBO}$	3.5 V
$P_{DISS}$	31.8 W @ $T_C = 25 \text{ }^\circ\text{C}$
$T_J$	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
$T_{STG}$	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$
$\theta_{JC}$	20 $^\circ\text{C/W}$

## PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

## CHARACTERISTICS $T_C = 25 \text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 1.0 \text{ mA}$	45			V
$BV_{CEO}$	$I_C = 20 \text{ mA}$	24			V
$BV_{EBO}$	$I_E = 0.25 \text{ mA}$	3.5			V
$I_{CBO}$	$V_{CB} = 28 \text{ V}$			0.45	mA
$h_{FE}$	$V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}$	15		120	---
$C_{ob}$	$V_{CB} = 28 \text{ V}$ $f = 1.0 \text{ MHz}$			5.0	pF
$P_G$ $\eta_D$	$V_{CC} = 28 \text{ V}$ $P_{OUT} = 1.0 \text{ W}$ $f = 400 \text{ MHz}$	13	60		dB %

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